

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.

## FAIRCHILD

SEMICONDUCTOR®

#### November 2013

FDB5800 — N-Channel Logic Level PowerTrench<sup>®</sup> MOSFET

# FDB5800

# N-Channel Logic Level PowerTrench<sup>®</sup> MOSFET 60 V, 80 A, 6 mΩ

#### Features

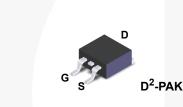
- $R_{DS(on)}$  = 4.6 m $\Omega$  (Typ.),  $V_{GS}$  = 10 V,  $I_D$  = 80 A
- High Performance Trench Technology for Extermly Low R<sub>DS(on)</sub>
- Low Gate Charge
- High Power and Current Handing Capability
- RoHs Compliant

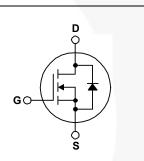
## Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### Applications

- Power tools
- Motor drives and Uninterruptible Power Supplies





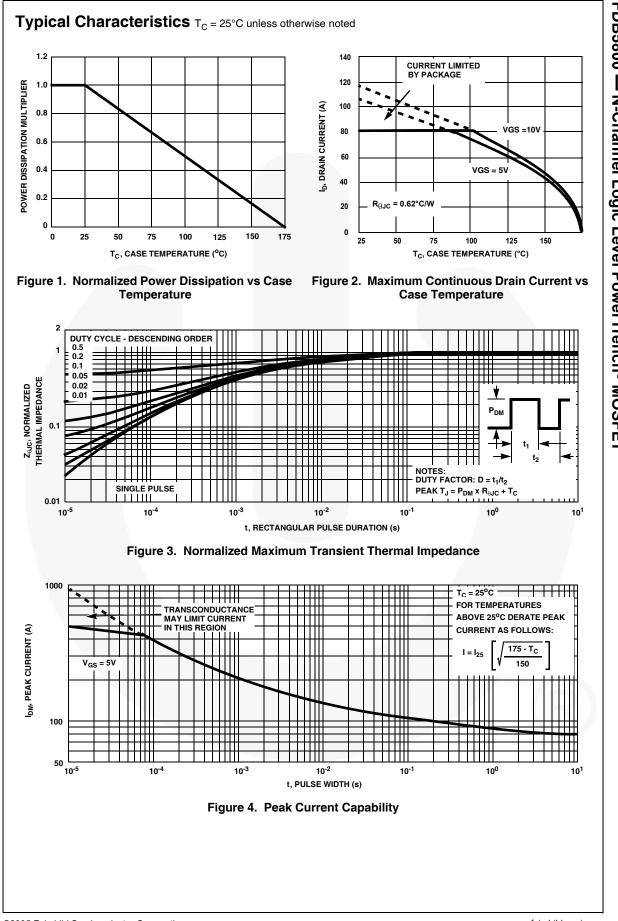
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

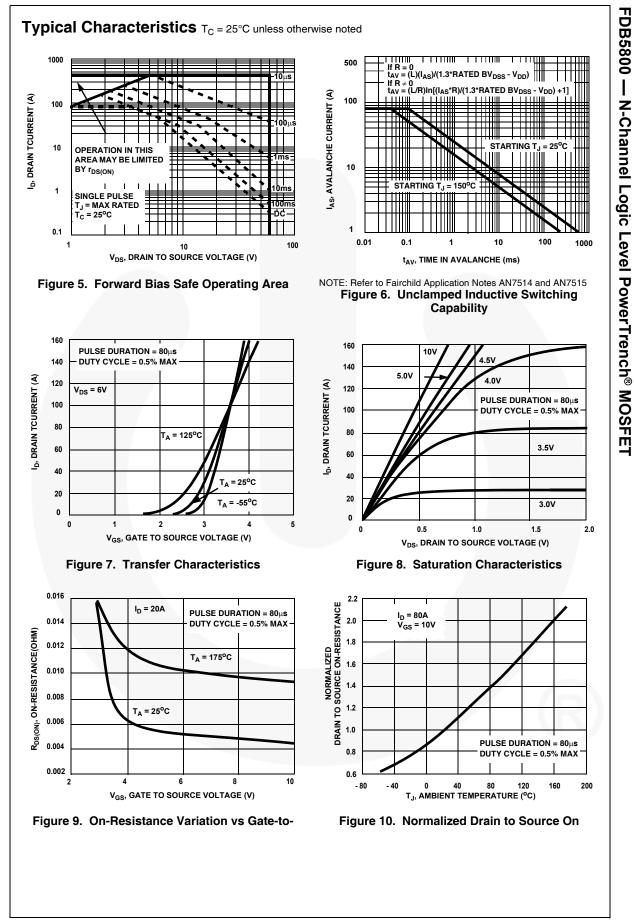
Symbol	Parameter		FDB5800	Unit
V <sub>DSS</sub>	Drain to Source Voltage		60	V
V <sub>GS</sub>	Gate to Source Voltage		±20	V
	Drain Current - Continuous (T <sub>C</sub> < 102 <sup>o</sup> C, V <sub>GS</sub> = 10 V)		80	А
I <sub>D</sub>	- Continuous ( $T_C < 90^{\circ}C$ , $V_{GS} = 5 V$ )		80	Α
	- Continuous ( $T_{amb}$ = 25°C, $V_{GS}$ = 10V, with $R_{\theta JA}$ = 43°C/W)		14	Α
	- Pulsed		Figure 4	Α
E <sub>AS</sub>	Single Pulse Avalanche Energy (	Note 1)	652	mJ
P <sub>D</sub>	- Power Dissipation		242	W
	- Derate above 25°C		1.61	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	- Operating and Storage Temperature		-55 to 175	°C

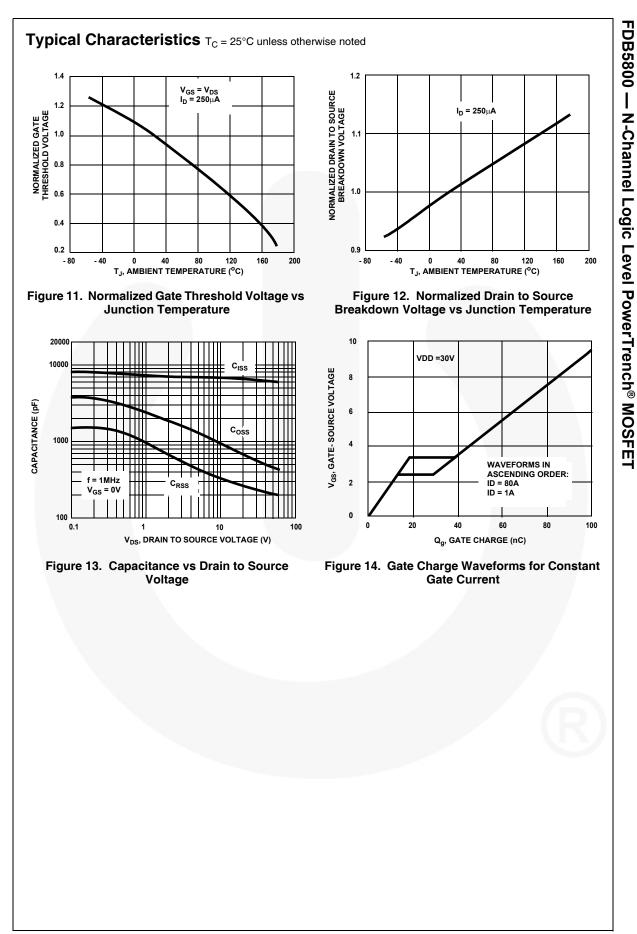
### **Thermal Characteristics**

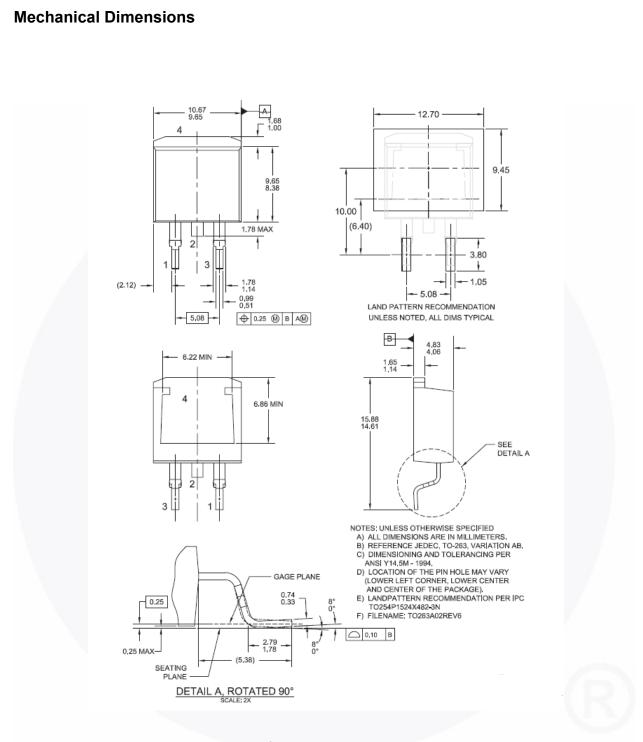
$R_{\theta JC}$	Thermal Resistance Junction to Case TO-263, Max.	0.62	°C/W
$R_{ hetaJA}$	Thermal Resistance Junction to Ambient TO-263, Max. (Note 2)	62.5	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance Junction to Ambient TO-263, 1in <sup>2</sup> copper pad area	43	°C/W

	Part Number Top Mark Pack		Packa	ge	Packing	Method	Reel	Size	Tape Wig	dth Qi	uantity
FDB5800 FDB5800					330		24 mm		800 units		
		1				1					
lectrica	al Chai	racteristics	T <sub>c</sub> = 25°C unles	s otherwise	noted.						
Symbol		Parameter			Test Co	nditions		Min.	Тур.	Max.	Unit
Off Chara	oteristio	<u> </u>									
	Drain to Source Breakdown Voltage							60	-	-	V
B <sub>VDSS</sub>	Zero Gate Voltage Drain Current Gate to Source Leakage Current		$I_D = 250 \ \mu A, V_{GS} = 0 \ V$ $V_{DS} = 48 \ V$			- 00	-	- 1	v		
I <sub>DSS</sub>			$V_{GS} = 0 V$ $T_{C} = 150^{\circ}C$			0°C	_	-	250	μA	
I <sub>GSS</sub>			$V_{CS} = -$	$V_{GS} = \pm 20 V$			-	-	±100	nA	
		-		- 63							
On Chara	cteristic	s								-	
V <sub>GS(TH)</sub>	Gate to S	Source Threshold \	/oltage		V <sub>DS</sub> , I <sub>D</sub> =			1.0	-	2.5	V
					A, V <sub>GS</sub> =			-	4.6	6.0	
					A, V <sub>GS</sub> =			-	5.8	7.2	-
r <sub>DS(ON)</sub>	Drain to	Source On Resista	ince		A, V <sub>GS</sub> =			-	5.5	7.0	mΩ
				I <sub>D</sub> = 80 T <sub>.1</sub> = 17	A, V <sub>GS</sub> = 75°C	= 10 V,		- 10 12.6			
Dynamic	Charact	eristics							<u> </u>		
C <sub>ISS</sub>	-	pacitance	_					-	6625	-	pF
C <sub>OSS</sub>		apacitance			15 V, V <sub>G</sub>	<sub>3</sub> = 0 V,	ŀ	-	628	-	pF
C <sub>RSS</sub>	-	Transfer Capacita	nce	f = 1 M	Hz		ŀ	-	262	-	pF
R <sub>G</sub>	Gate Res			$V_{CS} = 0$	0.5 V, f =	1 MHz		-	1.4	-	Ω
Q <sub>g(TOT)</sub>	Total Ga	te Charge at 10V		$V_{GS} = 0 V \text{ to } 10 V$			-	104	135	nC	
$Q_{g(5)}$		te Charge at 5V	_	$V_{cc} = 0 V to 5 V$			ŀ	-	55	72	nC
Q <sub>g(TH)</sub>		d Gate Charge	_	$V_{GS} = 0$	0 V to 1 \	V <sub>DD</sub> = 30 V I <sub>D</sub> = 80 A		-	6.0	-	nC
Q <sub>gs</sub>		Source Gate Charg	e	00		l <sub>D</sub> = 80 الـــــ ا <sub>a</sub> = 1.0	A	-	18.4	-	nC
Q <sub>gs2</sub>		arge Threshold to I				l <sub>g</sub> = 1.0	IIIA -	-	12.5	-	nC
Q <sub>gd</sub>	Gate to I	Drain "Miller" Charg	je	_			F	-	20.1	-	nC
<b>J</b> .											
Switching	g Charao	cteristics (V <sub>GS</sub>	= 5V)								
t <sub>ON</sub>	Turn-On	Time						-	-	62.1	ns
t <sub>d(ON)</sub>	Turn-On	Delay Time		V <sub>DD</sub> = 30 V, I <sub>D</sub> = 80 A			Γ	-	20.3	-	ns
	Rise Tim	е						-	22.0	-	ns
		urn-Off Delay Time		$V_{GS}$ = 5 V, $R_{GS}$ = 2 $\Omega$				-	27.1	-	ns
t <sub>r</sub>	Turn-Off	Delay Time		00					12.1		
t <sub>r</sub> t <sub>d(OFF)</sub>	Turn-Off Fall Time			00				-	12.1	-	ns
t <sub>r</sub> t <sub>d(OFF)</sub> t <sub>f</sub>	-	9						-	-	- 59.0	ns ns
t <sub>r</sub> t <sub>d(OFF)</sub> t <sub>f</sub> t <sub>OFF</sub>	Fall Time Turn-Off	9	stics					-	-	59.0	
t <sub>r</sub> t <sub>d(OFF)</sub> t <sub>f</sub> t <sub>OFF</sub> Drain-Sou	Fall Time Turn-Off	e Time de Characteri		I <sub>SD</sub> = 8	0 A			-	-	- 59.0 1.25	
t <sub>r</sub> t <sub>d(OFF)</sub> t <sub>f</sub> t <sub>OFF</sub>	Fall Time Turn-Off	Time						-	-		ns
t <sub>r</sub> t <sub>d(OFF)</sub> t <sub>f</sub> t <sub>OFF</sub> Drain-Sou	Fall Time Turn-Off urce Dio Source to	e Time de Characteri		<sub>SD</sub> = 8   <sub>SD</sub> = 4	0 A	/dt = 100 A	¥μs	-	-	1.25	ns V









#### Figure 15. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT263-002



Obsolete

Not In Production

Semiconductor. The datasheet is for reference information only.

Rev. 166

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UF0-7B